

/ Revised record

版本	修订日期	有修订的页码	修订涉及的内容	拟制	审核
			与刘哥确认功率 由 625 mW 改为 300mW	黄超	刘晓荣



/ Descriptions

□ 塑封封装 半导体三极管。Silicon PNP transistor in a SOT-23 Plastic Package.

/ Features

与 互补。

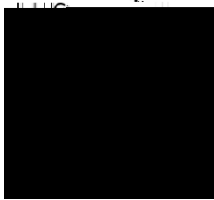
Complementary pair with L8050M.

/ Applications

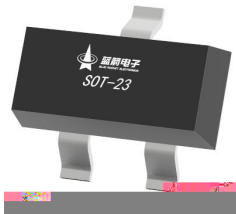
功率放大电路。

Power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 : Base

PIN 2 : Emitter

PIN 3 : Collector

/ h_{FE} Classifications & Marking

h_{FE}

/ Absolute Maximum Ratings(Ta=25)

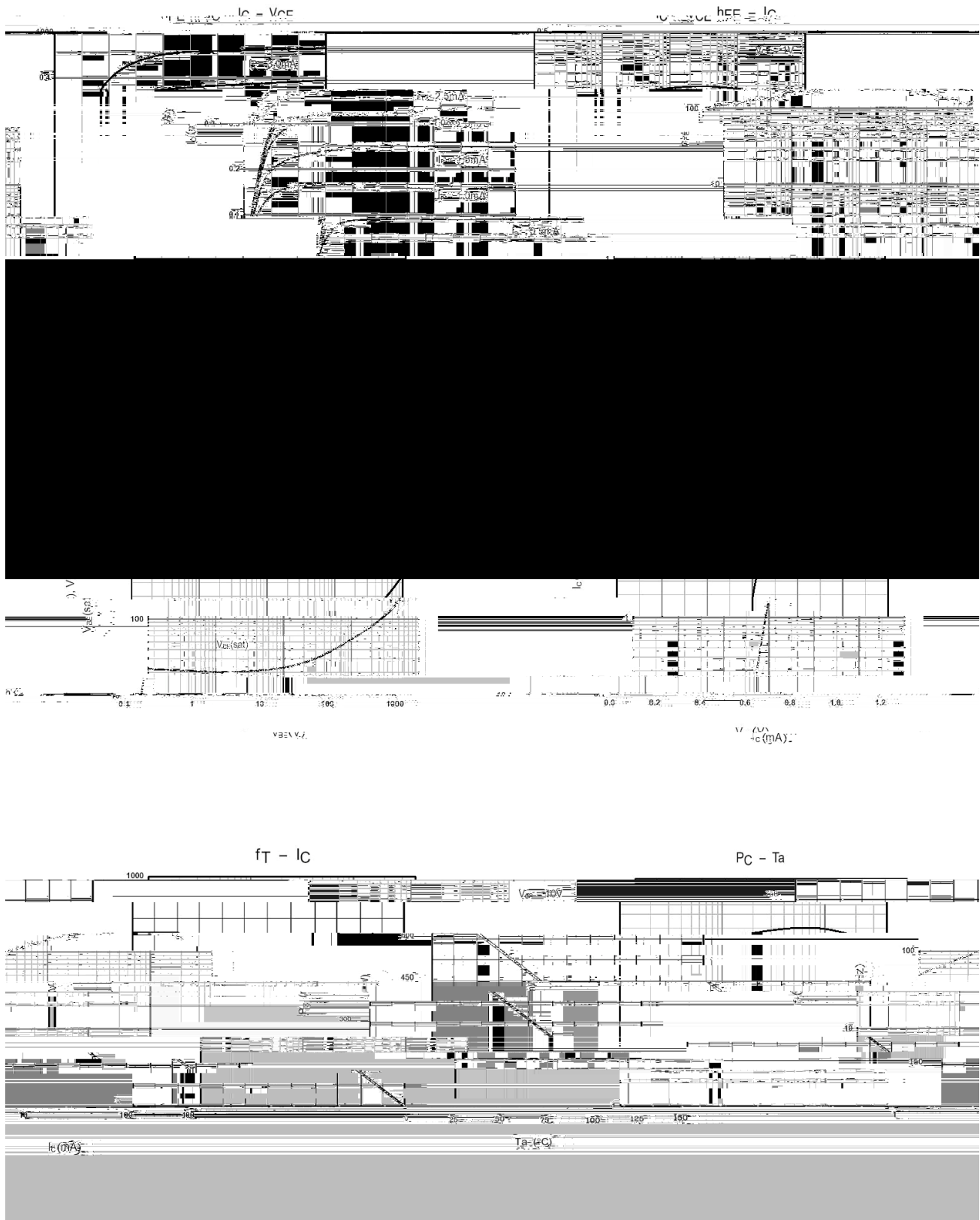
参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-1.5	A
Base Current - Continuous	I_B	-0.5	A
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

/ Electrical Characteristics(Ta=25)

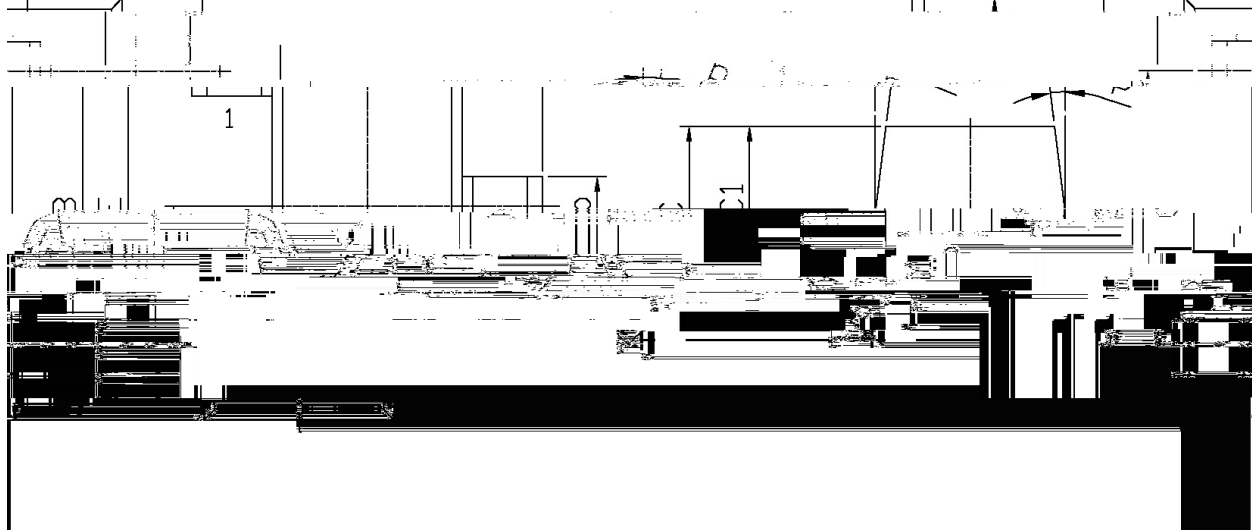
参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-0.1mA$ $I_E=0$	-30			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-2.0mA$ $I_B=0$	-20			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-0.1mA$ $I_C=0$	-6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30V$ $I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-6.0V$ $I_C=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-100mA$	85		300	
	$h_{FE(2)}$	$V_{CE}=-1.0V$ $I_C=-800mA$	40			
	$h_{FE(3)}$	$V_{CE}=-1.0V$ $I_C=-5.0mA$	45			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-800mA$ $I_B=-80mA$		-0.28	-0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-800mA$ $I_B=-80mA$		-0.98	-1.2	V
Base to Emitter Saturation Voltage	V_{BE}	$V_{CE}=-1.0V$ $I_C=-10mA$		-0.66	-1.0	V
Transition Frequency	f_T	$V_{CE}=-10V$ $I_C=-50mA$	100	200		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V$ $f=1.0MHz$ $I_E=0$		15		pF



/ Electrical Characteristic Curve

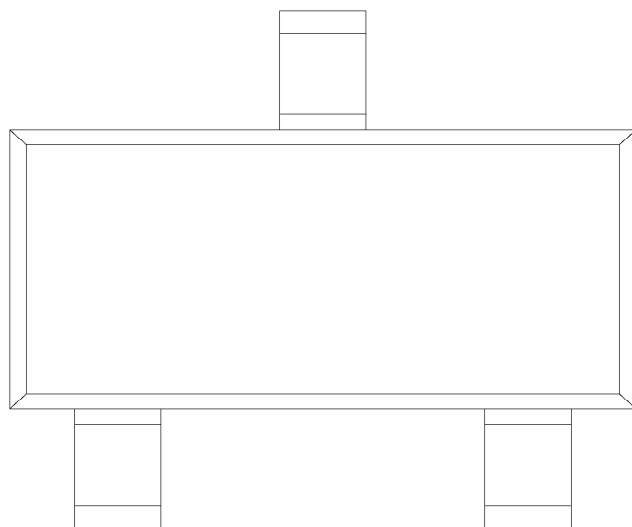


/ Package Dimensions



Dimensions		Symbol		Dimensions	
Max	Min	Max	Min	Symbol	Min
30Max		2.2	2.7	C	0.10
1.20		0.45	0.65	L1	0.90
0.20		1.45	1.50	E	0.35
K	0.0	0.10		B	2.70
M	0.20MIN			E	1.70
P	7°			E1	0.85
				b	0.35

/ Marking Instructions



说明：

H： 为公司代码

Y2： 为型号代码

B： 为 h_{FE} 分档代码

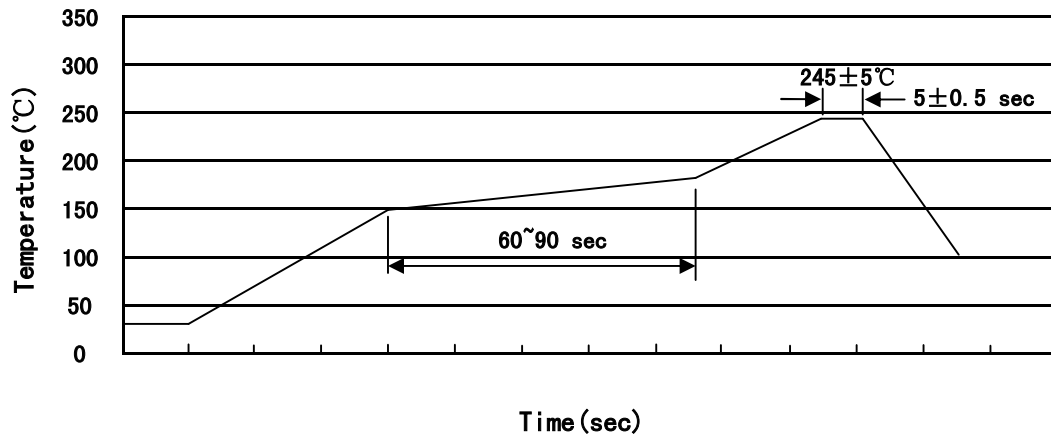
Note:

H: Company Code

Y2: Product Type Code

B: h_{FE}

() / **Temperature Profile for IR Reflow Soldering(Pb-Free)**



说明：

- 1、预热温度 150 ~ 180°C，时间 60 ~ 90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

/ **Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

/ **Packaging SPEC.**

卷盘包装 / REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7" x8	180×120×180	390×385×205

/ **Notices**